

SHDT373013

3A HERMETIC THIN DIODE
FAST RECOVERY

TECHNICAL DATA DATA SHEET 6052, Rev. -

AVAILABLE AS SS SSQ

# HERMETIC THIN DIODE Fast Recovery Rectifier

### **DESCRIPTION:**

Electrically Equivalent to 1N5418 and may be screened in line with MIL-PRF-19500/411 (see notes)

This low profile, hermetically sealed, fast recovery rectifier diode is manufactured using a JANS qualified wafer fab and is designed for space solar array applications. The silver-plated flat leads are designed for ease in welding to solar array PCBs.

#### **FEATURES / BENEFITS:**

#### **MAXIMUM RATINGS:**

- ✓ Silver plated flat leads
- ✓ Hermetic, cavity ceramic package
- ✓ JANS Equivalent screening and QCI available
- ✓ Operating & Storage Temperature: -65°C to +175°C
- ✓ Thermal Resistance: 27°C/W (junction to lead)
- ✓ Scope Display on 100% of parts

#### **ELECTRICAL CHARACTERISTICS**

MAX. RATINGS / ELECTRICAL CHARACTERISTICS All ratings are at T<sub>A</sub> = 25°C unless otherwise specified.

RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	I <sub>R</sub> = 50µA I <sub>R</sub> = 50µA, T <sub>A</sub> = -55°C	-	-	400 400	V dc
Average DC Output Current (Io)*	$T_A = +55^{\circ}C$ $T_A = +100^{\circ}C$	-	-	3 2	А
Peak Single Cycle Surge Current (I <sub>FSM</sub> )	t <sub>p</sub> = 8.3 ms Single Half Cycle Sine Wave, superimposed on 2A dc, 400V DC	-	-	80	A (pk.)
Operating and Storage Temp. (Top & Tstg)	-	-65	-	+175	°C
Maximum Forward Voltage (V <sub>F</sub> )	I <sub>F</sub> = 1.5A I <sub>F</sub> = 9A I <sub>F</sub> = 0.5A, T <sub>A</sub> = -55°C	0.5 0.6 0.5	-	1.2 1.5 1.4	Volts
Maximum Instantaneous Reverse Current at PIV (I <sub>R</sub> )	T <sub>A</sub> = 25° C T <sub>A</sub> = 100° C	-	-	1 20	μΑ
Reverse Recovery Time (t <sub>RR</sub> )	I <sub>f</sub> = 0.5A, I <sub>r</sub> = 1.0A, I <sub>rr</sub> = 0.25A	-	-	150	nsec
Capacitance (C)	V <sub>R</sub> = 4V dc, 100KHz ≤ f ≤ 1MHz	-	-	165	pF
Thermal Resistance (θ <sub>J</sub> L)	Junction to Lead d = 0.375"			27	°C/W

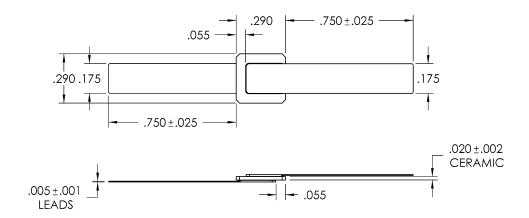
Note \* - Derate linearly at  $22\text{mA}/^{\circ}\text{C}$  from  $55^{\circ}\text{C} \le T_{\text{A}} \le 100^{\circ}\text{C}$ ; at  $26.7\text{mA}/^{\circ}\text{C}$  from  $100^{\circ}\text{C} \le T_{\text{A}} \le 175^{\circ}\text{C}$  Due to low profile package, Breakdown voltage test cannot be performed. Instead, additional leakage current is done at 440V with a  $50\mu\text{A}$  limit.

In addition, scope display test is not performed since this test requires testing over the breakdown voltage.

<u>SENSITRON</u> SEMICONDUCTOR 3A HERMETIC THIN DIODE FAST RECOVERY

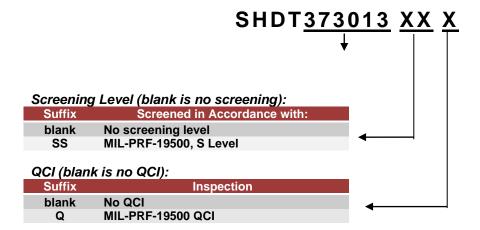
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# PACKAGE DIMENSIONS (inches/mm)



PKG: TFP-1

## PART ORDERING INFORMATION



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